
2SC4501(L)/(S)

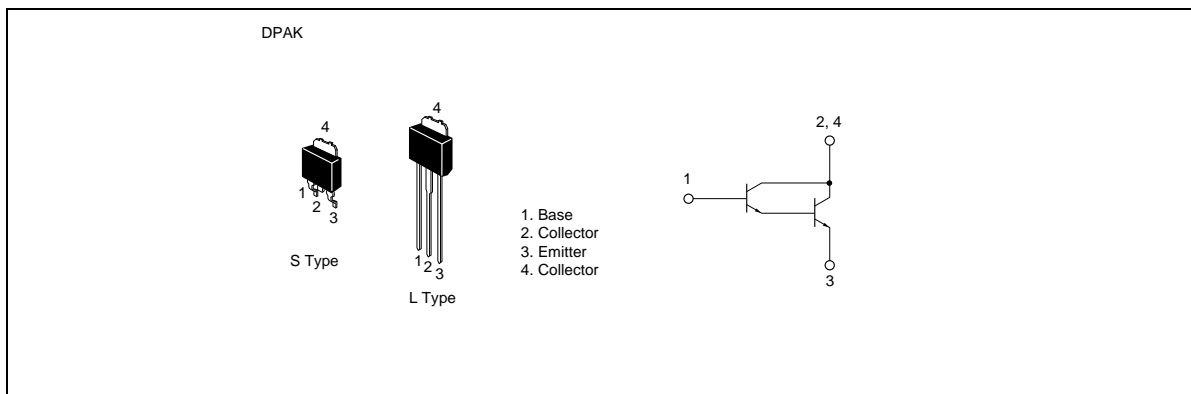
Silicon NPN Epitaxial

HITACHI

Application

High gain amplifier and medium speed switching

Outline



2SC4501(L)/(S)

Absolute Maximum Ratings (Ta = 25°C)

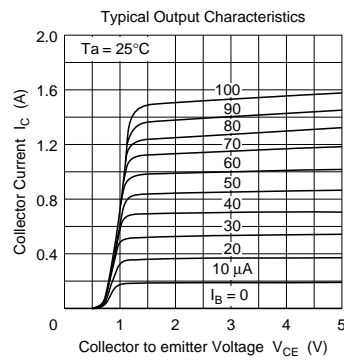
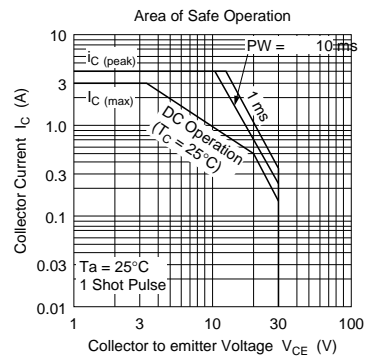
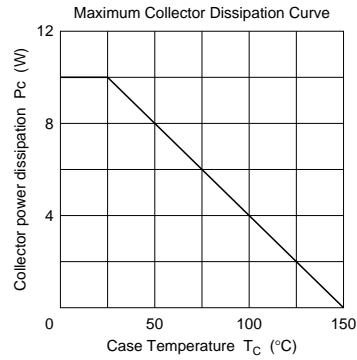
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	30	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I_C	3	A
Collector peak current	$I_{C(peak)}$	4	A
Collector power dissipation	P_C^{*1}	10	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	–55 to +150	°C

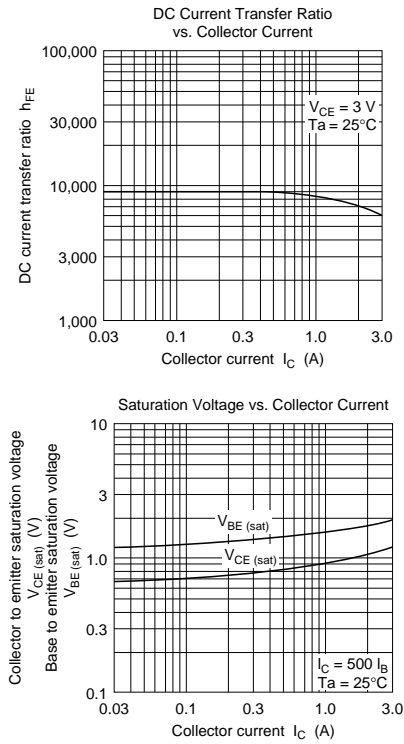
Note: 1. Value at $T_C = 25^\circ\text{C}$.

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	V	$I_C = 0.1\text{ mA}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	—	—	V	$I_C = 1\text{ mA}$, $R_{BE} = _$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 0.1\text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CEO}	—	—	20	μA	$V_{CB} = 24\text{ V}$, $R_{BE} = _$
DC current transfer ratio	h_{FE}	2000	—	50000		$V_{CE} = 3\text{ V}$, $I_C = 1.5\text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.5	V	$I_C = 1.5\text{ A}$, $I_B = 3\text{ mA}^{*1}$
	$V_{CE(sat)}$	—	—	2.0		$I_C = 3\text{ A}$, $I_B = 30\text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	2.0	V	$I_C = 1.5\text{ A}$, $I_B = 3\text{ mA}^{*1}$
	$V_{BE(sat)}$	—	—	3.5		$I_C = 3\text{ A}$, $I_B = 30\text{ mA}^{*1}$
Turn on time	t_{on}	—	0.4	—	μs	$I_C = 1.5\text{ A}$,
Turn off time	t_{off}	—	1.2	—	μs	$I_{B1} = -I_{B2} = 3\text{ mA}$,
Storage time	t_{stg}	—	0.8	—	μs	$V_{CC} = 30\text{ V}$

Note: 1. Pulse test.





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